Product data sheet

1. General description

Dual common cathode power Schottky diode designed for high frequency switched mode power supplies in a TO220 plastic package.





2. Features and benefits

- Trench structure
- High junction temperature up to 150 °C
- Low forward voltage drop, negligible switching losses
- · High efficiency

3. Applications

- DC to DC converters
- · Freewheeling diode
- OR-ing diode
- · Switched mode power supply rectifier

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Notes | Values | | | Unit | | | | | |
|----------------|---------------------------------|--|-------|--------|------|------|------|--|--|--|--|--|
| Absolute | Absolute maximum rating | | | | | | | | | | | |
| V_{RRM} | repetitive peak reverse voltage | | | | 100 | | V | | | | | |
| $I_{F(AV)}$ | average forward current | δ = 0.5 ; square-wave pulse; T _{mb} ≤ 137 °C; per diode; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u> | | 5 | | | А | | | | | |
| $I_{O(AV)}$ | average output current | δ = 0.5 ; square-wave pulse; $T_{mb} \le 135$ °C; both diodes conducting | | 10 | | | А | | | | | |
| Symbol | Parameter | Conditions | Notes | Min | Тур | Max | Unit | | | | | |
| Static ch | aracteristics | | | | | | | | | | | |
| V_{F} | forward voltage | $I_F = 5 \text{ A}; T_j = 25 \text{ °C}; \text{ per diode}; Fig. 6$ | | - | 0.67 | 0.77 | V | | | | | |
| I _R | reverse current | $V_R = 100 \text{ V}$; $T_j = 25 \text{ °C}$; per diode; Fig. 7; Fig. 8 | | - | 2.5 | 15 | μA | | | | | |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------------------------------|--|------------------|
| 1 | A1 | anode 1 | mb | |
| 2 | K | cathode | | A1 A2 |
| 3 | A2 | anode 2 | | Κ Κ sym125 |
| mb | К | mounting base; connected to cathode | | gjiii 2 |

6. Ordering information

Table 3. Ordering information

| Type number | Package name | Orderable part number | Packing method | Small packing quantity | Package version | Package issue date |
|-------------|--------------|-----------------------|----------------|------------------------|-----------------|--------------------|
| WN3S10100C | TO220 | WN3S10100CQ | Tube | 50 | SOT78 | 13-Jun-2008 |

7. Marking

Table 4. Marking codes

| Type number | Marking codes |
|-------------|----------------|
| WN3S10100C | WN3S10 100C |

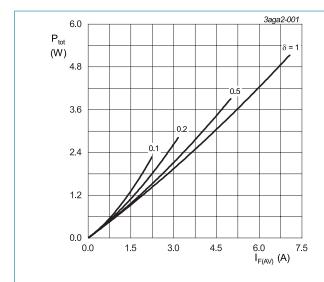
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

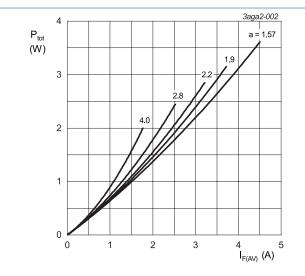
| Symbol | Parameter | Conditions | Notes | Values | Unit |
|--------------------|-------------------------------------|--|-------|------------|------|
| V_{RRM} | repetitive peak reverse voltage | | | 100 | V |
| V_{RWM} | crest working reverse voltage | | | 100 | V |
| V_R | reverse voltage | DC | | 100 | V |
| I _{F(AV)} | average forward current | δ = 0.5 ; square-wave pulse; T _{mb} ≤ 137 °C; per diode; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u> | | 5 | Α |
| $I_{O(AV)}$ | average output current | δ = 0.5 ; square-wave pulse; $T_{mb} \le 135$ °C; both diodes conducting | | 10 | А |
| I _{FSM} | non-repetitive peak forward current | t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4 | | 120 | А |
| | | t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode | | 132 | А |
| T _{stg} | storage temperature | | | -40 to 150 | °C |
| T _j | junction temperature | | [1] | -40 to 150 | °C |

[1] The heat generated must be less than the thermal conductivity from Junction to Ambient: $dP_{tot}/dT_j < 1/R_{th(j-a)}$



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$ V_o = 0.591 V; R_s = 0.0190 Ω

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode



a = form factor = $I_{F(RMS)}$ / $I_{F(AV)}$ V_o = 0.591 V; R_s = 0.0190 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values; per diode

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Dual power Schottky diode

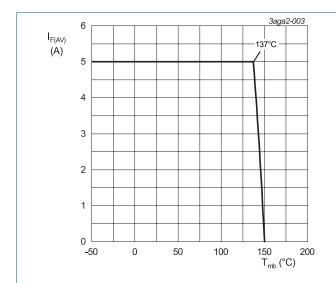


Fig. 3. Average forward current as a function of mounting base temperature; maximum values; per diode

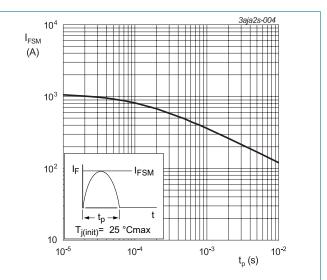


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values; per diode

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Notes | Min | Тур | Max | Unit |
|-----------------------|--|------------------------|-------|-----|-----|-----|------|
| $R_{\text{th(j-mb)}}$ | thermal resistance from junction to | per diode; Fig. 5 | | - | - | 3.3 | K/W |
| | mounting base | both diodes conducting | | - | - | 1.9 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient free air | in free air | | - | 60 | - | K/W |

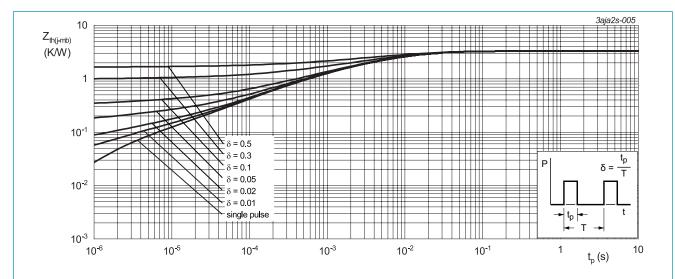
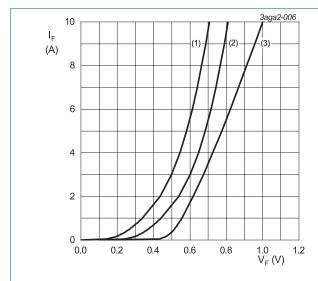


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration; maximum values; per diode

10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Notes | Min | Тур | Max | Unit |
|----------------|-----------------|--|-------|-----|------|------|------|
| Static ch | aracteristics | | | | | | |
| V_{F} | forward voltage | $I_F = 5 \text{ A}$; $T_j = 25 \text{ °C}$; per diode; Fig. 6 | | - | 0.67 | 0.77 | V |
| | | I _F = 5 A; T _j = 125 °C; per diode; <u>Fig. 6</u> | | - | 0.62 | - | V |
| I _R | reverse current | $V_R = 100 \text{ V}; T_j = 25 ^{\circ}\text{C}; \text{ per diode}; $ Fig. 7; Fig. 8 | | - | 2.5 | 15 | μA |
| | | $V_R = 100 \text{ V}; T_j = 125 ^{\circ}\text{C}; \text{ per diode}; $ Fig. 7; Fig. 8 | | - | 1.7 | 10 | mA |

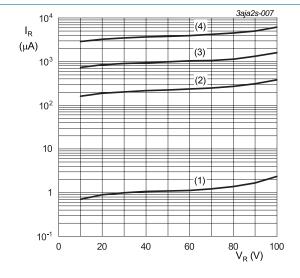


 $V_o = 0.591 \text{ V}; R_s = 0.0190 \Omega$

(1) T_j = 150 °C; typical values (2) T_j = 150 °C; maximum values

(3) $T_i = 25$ °C; maximum values

Fig. 6. Forward current as a function of forward voltage; per diode



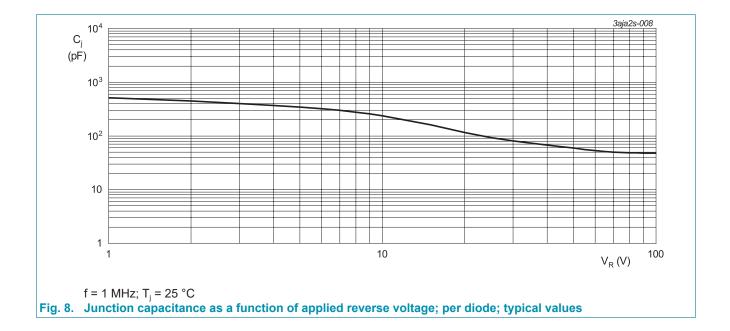
(1) T_i = 25 °C; typical values

(2) $T_j = 100$ °C; typical values (3) $T_j = 125$ °C; typical values (4) $T_j = 150$ °C; typical values

Fig. 7. Reverse leakage current as a function of reverse voltage; per diode; typical values

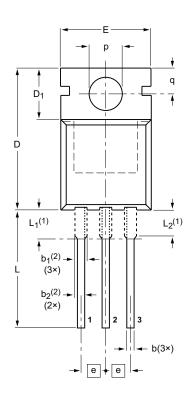
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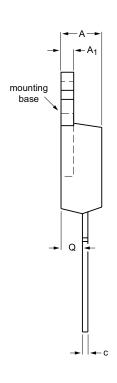
Dual power Schottky diode



11. Package outline







0 5 10 mm scale

DIMENSIONS (mm are the original dimensions)

| UNIT | A | A ₁ | b | b ₁ ⁽²⁾ | b ₂ ⁽²⁾ | С | D | D ₁ | E | е | L | L ₁ ⁽¹⁾ | L ₂ ⁽¹⁾ max. | р | q | Q |
|------|------------|----------------|------------|-------------------------------|-------------------------------|------------|--------------|----------------|-------------|------|--------------|-------------------------------|---------------------------------------|------------|------------|------------|
| mm | 4.7 4.1 | 1.40 1.25 | 0.9 0.6 | 1.6 1.0 | 1.3 1.0 | 0.7 0.4 | 16.0 15.2 | 6.6 5.9 | 10.3 9.7 | 2.54 | 15.0 12.8 | 3.30 2.79 | 3.0 | 3.8 3.5 | 3.0 2.7 | 2.6 2.2 |

Notes

- 1. Lead shoulder designs may vary.
- Dimension includes excess dambar.

| OUTLINE | | REFER | ENCES | EUROPEAN | ISSUE DATE |
|---------|-----|-----------------|-------|------------|---------------------------------|
| VERSION | IEC | JEDEC | JEITA | PROJECTION | 1330E DATE |
| SOT78 | | 3-lead TO-220AB | SC-46 | | 08-04-23 08-06-13 |

12. Legal information

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| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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WN3S10100C

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